

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L6	1427	(Dainippon near2 screen).as.	US-PGPUB; USPAT	OR	ON	2006/01/17 16:51
L7	14	L6 and (wet near2 etch\$3)	US-PGPUB; USPAT	OR	ON	2006/01/17 16:51
S17	2	"20040188386"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/14 10:07
S18	13	(takashi near2 izuta).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/14 10:06
S19	29159	216/83.ccls. 156/345.27.ccls. "237"/\$.ccls. 156/345.11.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/14 10:13
S20	1485	216/83.ccls. 156/345.27.ccls. 156/345.11.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/14 10:53
S21	112263	(etch\$3 strip\$3) near3 (wet liquid acid chemical)	US-PGPUB; USPAT	OR	ON	2006/01/14 11:59
S22	6097	S21 and (phosphoric and plurality)	US-PGPUB; USPAT	OR	ON	2006/01/14 16:30
S23	623	S22 and transport	US-PGPUB; USPAT	OR	ON	2006/01/14 10:49
S24	272	S23 and sulphuric	US-PGPUB; USPAT	OR	ON	2006/01/14 10:49
S25	1915	S21 and (phosphoric and (plural\$3 near3 (substrate wafer)))	US-PGPUB; USPAT	OR	ON	2006/01/14 10:52
S26	118	S25 and ("216"/\$.ccls. "118"/\$.ccls. 156/345.\$2.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/14 12:22
S27	83820	(etch\$3 strip\$3) near3 (wet liquid acid)	US-PGPUB; USPAT	OR	ON	2006/01/14 11:59
S28	1560	S21 and (sulphuric and (plural\$3 near3 (wafer substrate)))	US-PGPUB; USPAT	OR	ON	2006/01/14 12:00

S29	142	S28 and ("216"/\$.ccls. "118"/\$.ccls. 156/345.\$2.cccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/14 12:01
S30	38	S29 and (control near4 (time temperature))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/14 12:01
S31	109977	"216"/\$.ccls. "118"/\$.ccls. 156/345. \$2.cccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/14 12:23
S32	7095	S31 and ((wet liquid acid) near3 etch\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/14 12:24
S33	4516	S32 and control\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/14 14:36
S34	1160	S33 and (phosphoric sulphuric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/14 12:28
S35	280	S33 and (phosphoric and sulphuric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/14 12:28
S36	994	S32 and (control\$3 near4 ((substrate wafer) same3 (holder support)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/14 13:06

S37	195	S36 and (sulphuric phosphoric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/14 16:41
S38	167	S32 and (control\$3 and ((substrate wafer) near3 transport))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/14 14:38
S39	5	S38 and (phosphoric and sulphuric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/14 14:39
S40	185	S32 and ((substrate wafer) near3 transport)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/14 14:39
S41	5	S40 and (phosphoric and sulphuric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/14 14:39
S42	159	S32 and ((substrate wafer) near2 transport)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/14 14:39
S43	2	"5547896".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/14 15:52
S44	14	S20 and (etch\$3 and sulphuric and (heat near treat\$3))	US-PGPUB; USPAT	OR	ON	2006/01/14 16:33
S45	277	S20 and ((liquid wet) near4 etch\$3)	US-PGPUB; USPAT	OR	ON	2006/01/14 16:33
S46	2	S45 and (sulphuric near4 (heat\$3 hot))	US-PGPUB; USPAT	OR	ON	2006/01/14 16:34
S47	4	(wet near2 etch) near4 (sulphuric and hot)	US-PGPUB; USPAT	OR	ON	2006/01/14 16:48

S48	2	(wet near2 etch) near4 (sulphuric near hot)	US-PGPUB; USPAT	OR	ON	2006/01/14 17:02
S49	0	(wet near2 etch) near4 ((substrate wafer) near2 (holder support) same heater)	US-PGPUB; USPAT	OR	ON	2006/01/14 17:04
S50	0	(wet near2 etch) near4 ((substrate wafer) near2 (holder support) and heater)	US-PGPUB; USPAT	OR	ON	2006/01/14 17:05
S51	11052	((substrate wafer) near2 (holder support) and heater)	US-PGPUB; USPAT	OR	ON	2006/01/14 17:05
S52	1836	((substrate wafer) near2 (holder support) near4 heater)	US-PGPUB; USPAT	OR	ON	2006/01/14 17:17
S53	153	S52 and (wet near etch\$3)	US-PGPUB; USPAT	OR	ON	2006/01/14 17:07
S54	3	S52 same (wet near etch\$3)	US-PGPUB; USPAT	OR	ON	2006/01/14 17:17
S55	2066	((substrate wafer) near2 (holder support) near5 heater)	US-PGPUB; USPAT	OR	ON	2006/01/14 17:17
S56	3	S55 same (wet near etch\$3)	US-PGPUB; USPAT	OR	ON	2006/01/14 17:18
S57	4290	((substrate wafer) near2 (holder support) same heater)	US-PGPUB; USPAT	OR	ON	2006/01/14 17:21
S58	10	S57 same (wet near etch\$3)	US-PGPUB; USPAT	OR	ON	2006/01/14 17:18
S59	1687	((substrate wafer) near2 (holder support) same heater)	EPO; JPO; DERWENT	OR	ON	2006/01/14 17:22
S60	2	S59 and (wet near etch\$3)	EPO; JPO; DERWENT	OR	ON	2006/01/14 17:22
S61	319	((substrate wafer) near (holder support) near2 heater)	EPO; JPO; DERWENT	OR	ON	2006/01/14 17:30
S62	0	S61 and (wet near etch\$3)	EPO; JPO; DERWENT	OR	ON	2006/01/14 17:22
S63	18	S61 and etch\$3	EPO; JPO; DERWENT	OR	ON	2006/01/14 18:30
S64	2010	(Dainippon near2 screen)	US-PGPUB; USPAT	OR	ON	2006/01/14 18:31
S65	1427	(Dainippon near2 screen).as.	US-PGPUB; USPAT	OR	ON	2006/01/14 18:31
S66	14	S65 and (wet near2 etch\$3)	US-PGPUB; USPAT	OR	ON	2006/01/14 18:31
S67	17	S18 or S66	US-PGPUB; USPAT	OR	ON	2006/01/14 18:31

S68	8	"6446647".pn. "5421905".pn. "5406807".pn. "4039737".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/17 10:51
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